

isc Silicon NPN Power Transistor

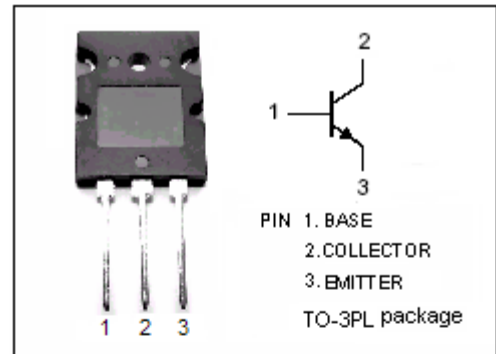
BU2532AL

DESCRIPTION

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 800V$  (Min)
- High Switching Speed

APPLICATIONS

- Designed for use in horizontal deflection circuits of high resolution monitors.

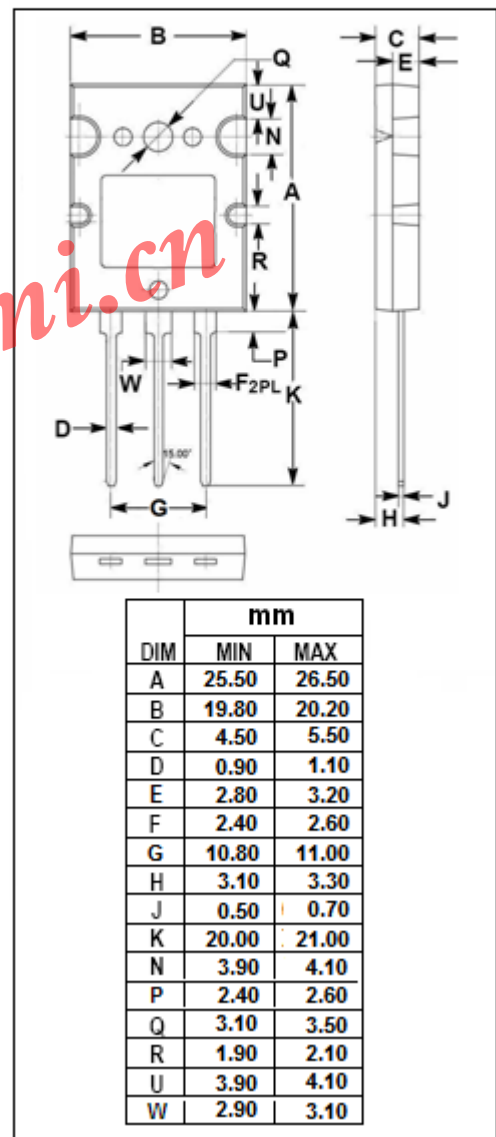


ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CES}$	Collector- Emitter Voltage( $V_{BE} = 0$ )	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	7.5	V
$I_C$	Collector Current- Continuous	16	A
$I_{CM}$	Collector Current-Peak	40	A
$I_B$	Base Current- Continuous	10	A
$I_{BM}$	Base Current-Peak	15	A
$P_C$	Collector Power Dissipation @ $T_c=25^{\circ}C$	125	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^{\circ}C/W$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=7\text{A}; I_B=1.17\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=7\text{A}; I_B=1.17\text{A}$			1.0	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=1500\text{V}; V_{BE}=0$ $V_{CE}=1500\text{V}; V_{BE}=0; T_C=125^{\circ}\text{C}$			1.0 2.0	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=7.5\text{V}; I_C=0$			1.0	mA
$h_{FE-1}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$		17		
$h_{FE-2}$	DC Current Gain	$I_C=7\text{A}; V_{CE}=5\text{V}$	6		12.5	

## Switching times

$t_{stg}$	Storage Time	$I_C=7\text{A}, I_{B(end)}=1\text{A}; L_C=100\mu\text{H};$ $V_{CC}=138\text{V}; C_{fb}=3\text{nF}$			1.8	$\mu\text{s}$
$t_f$	Fall Time				0.1	$\mu\text{s}$